

Supporting Information for:

Controllable Fabrication of Ternary ZnIn_2S_4 Nanosheet Array Film for Bulk Heterojunction Solar Cells

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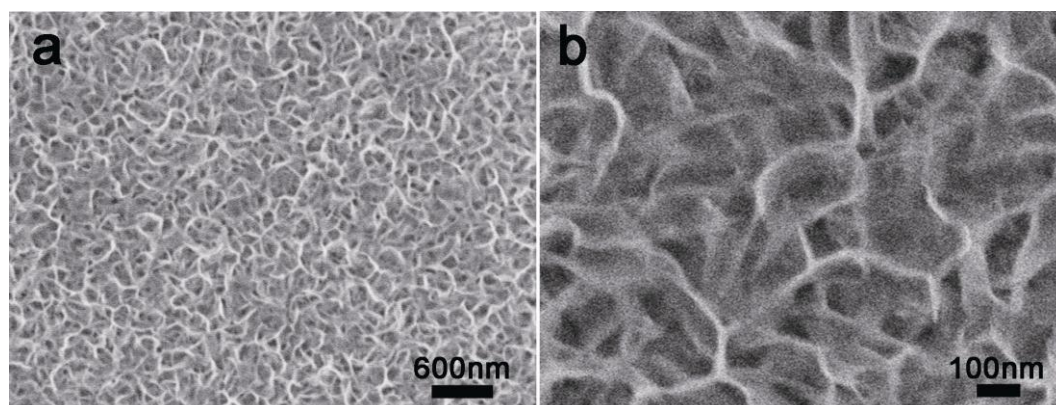


Figure S1. SEM images of as-prepared ZnIn_2S_4 nanosheet film by solvothermal treatment of a 20 nm Zn/In film and 0.5 mmol S powders at 180 °C for 24 h.

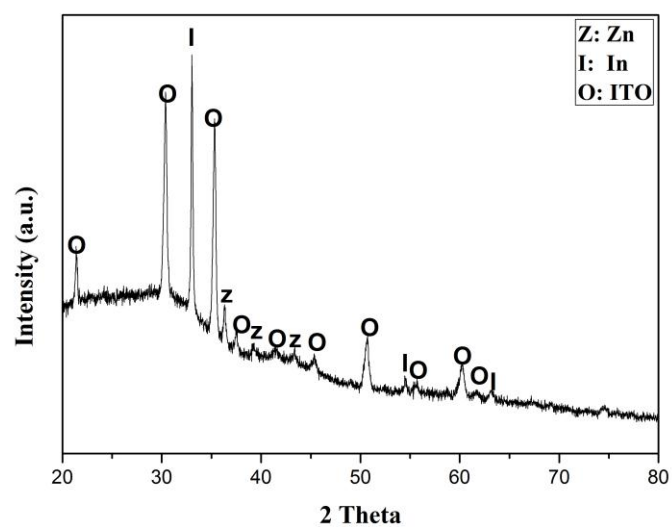


Figure S2. X-ray diffraction (XRD) pattern of original zinc/indium film with thickness of 80 nm by magnetron sputtering before solvothermal treatment.

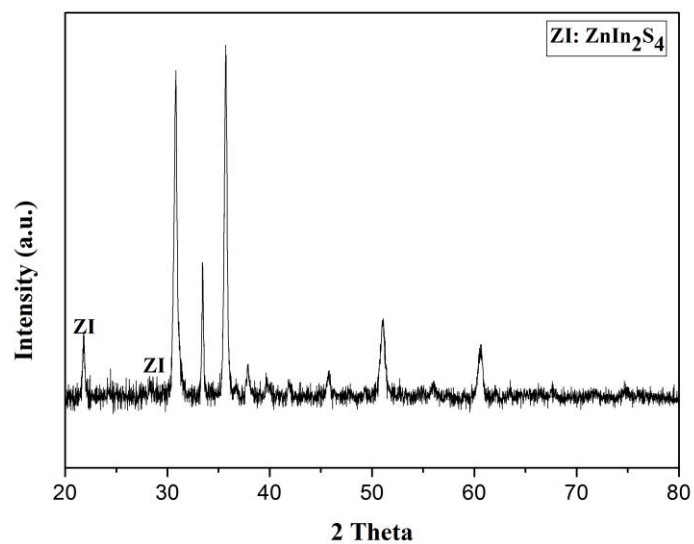


Figure S3. X-ray diffraction (XRD) pattern of the ZnIn₂S₄ film obtained by solvothermal treatment of 80 nm thick Zn/In bimetallic film and 0.5 mmol S powders at 180°C for 12 h.

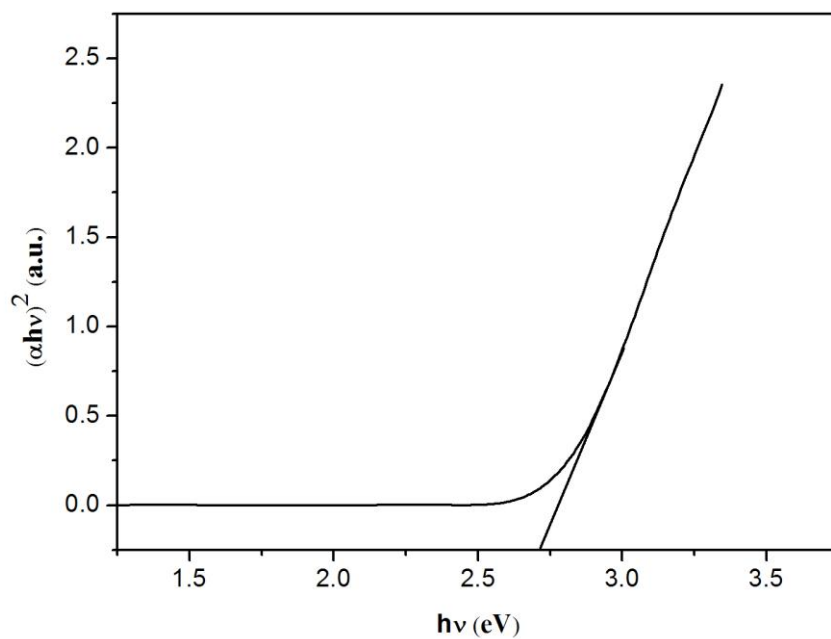


Figure S4. The corresponding $(\alpha h\nu)^2$ vs. $h\nu$ curve.

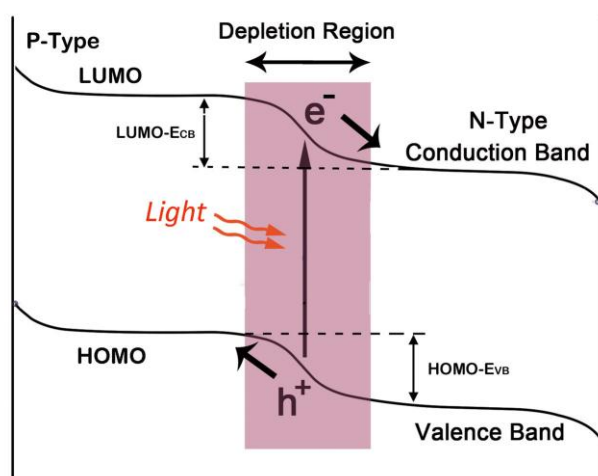


Figure S5. Schematic drawing of the donor and acceptor energy levels.